



General Description

- 100% UIS Tested
- Super Trench Technology
- Surface-mounted package
- MSL1
- T_j max 175°C

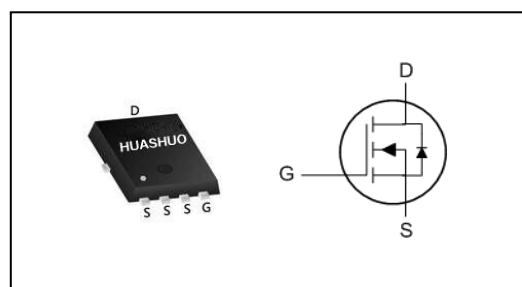
Product Summary

V_{DS}	30	V
$R_{DS(ON),MAX}$	0.5	$m\Omega$
I_D	197	A

Applications

- Motor drivers
- DC/DC Converters

PRPAK5X6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	197	A
I_{DM}	Pulsed Drain Current ²	788	A
EAS	Single Pulse Avalanche Energy ³	420	mJ
I_S	Avalanche Current	197	A
$P_D @ T_c = 25^\circ C$	Total Power Dissipation ⁴	35	W
T_{STG}	Storage Temperature Range	-55 to 175	°C
T_J	Operating Junction Temperature Range	-55 to 175	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62.5	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	3.5	°C/W



N-Ch 30V Fast Switching MOSFETs

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30	---	---	V
R _{DSON}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =50A	---	0.45	0.5	mΩ
		V _{GS} =4.5V , I _D =30A	---	0.75	0.85	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1	---	2	V
I _{bss}	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =24V , V _{GS} =0V , T _J =85°C	---	---	30	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
Q _g	Total Gate Charge	V _{DS} =15V , V _{GS} =10V , I _D =50A	---	142	---	nC
Q _{gs}	Gate-Source Charge		---	26	---	
Q _{gd}	Gate-Drain Charge		---	27	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V , V _{GS} =10V , R _G =4.5Ω, R _L =0.3Ω, I _D =50A	---	12.3	---	ns
T _r	Rise Time		---	92	---	
T _{d(off)}	Turn-Off Delay Time		---	158	---	
T _f	Fall Time		---	119	---	
C _{iss}	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz	---	8080	---	pF
C _{oss}	Output Capacitance		---	3466	---	
C _{rss}	Reverse Transfer Capacitance		---	236	---	

Diode Characteristics

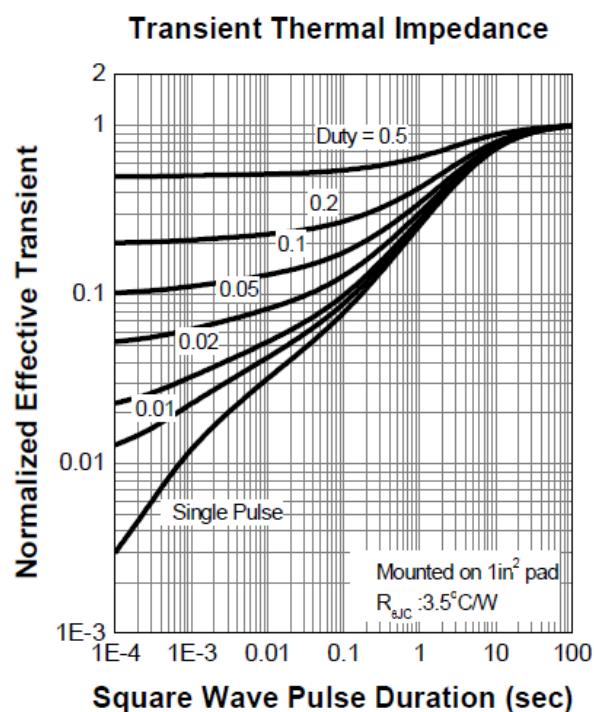
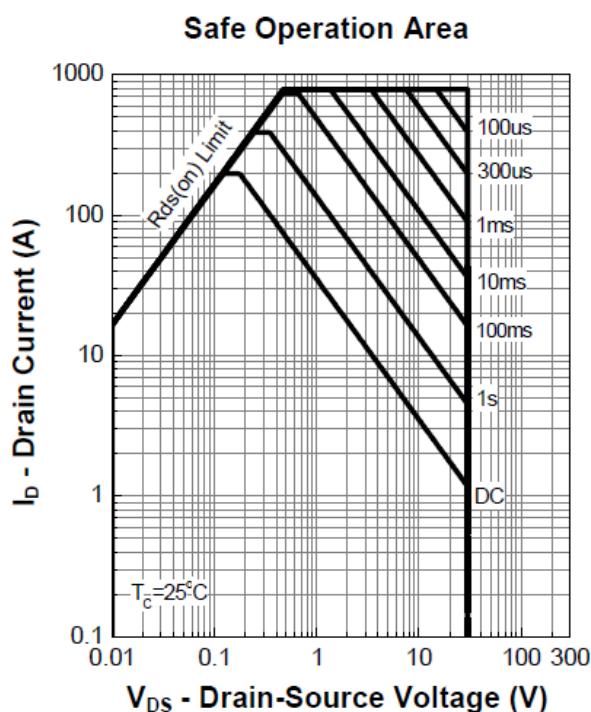
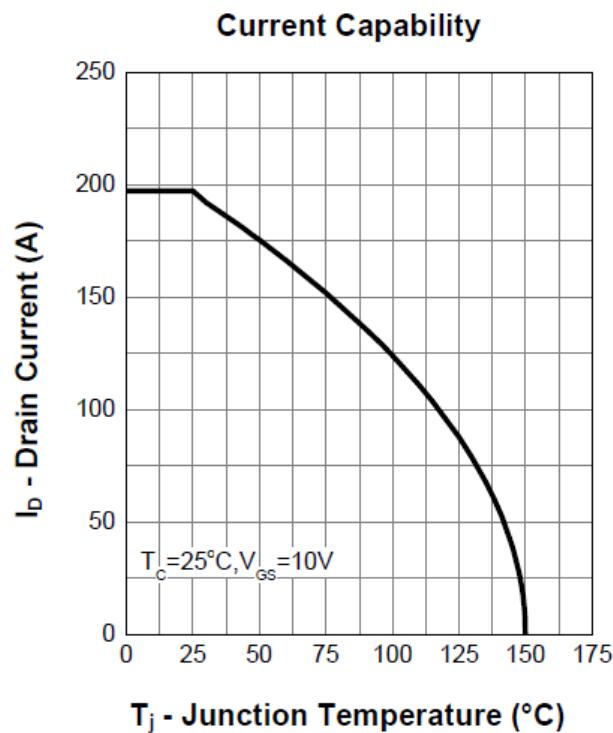
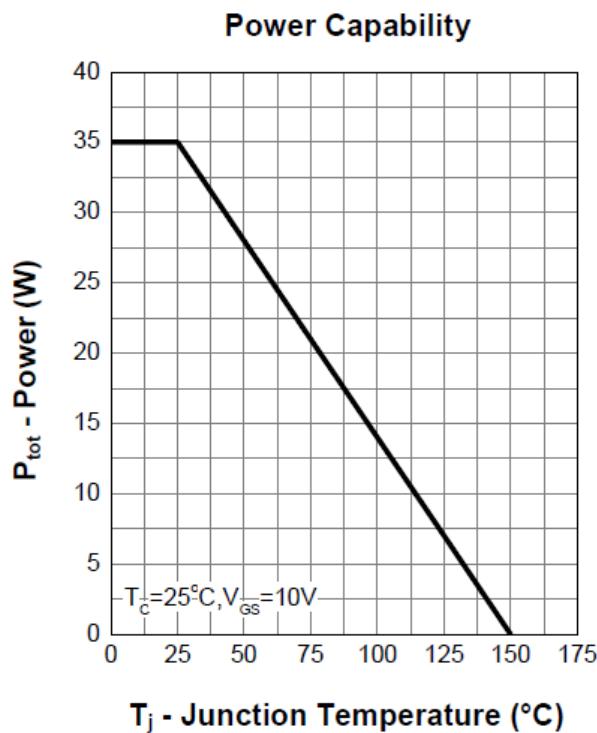
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
t _{rr}	Reverse Recovery Time	I _{sd} =30A, dI _{sd} /dt=100A/us	---	83	---	nS
Q _{rr}	Reverse Recovery Charge		---	113	---	nC
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _s =50A , T _J =25°C	---	---	1.3	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

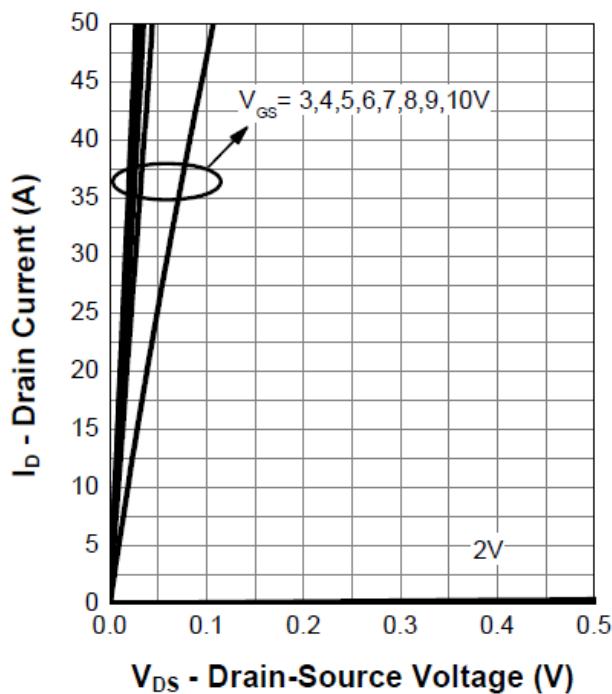


Typical Characteristics

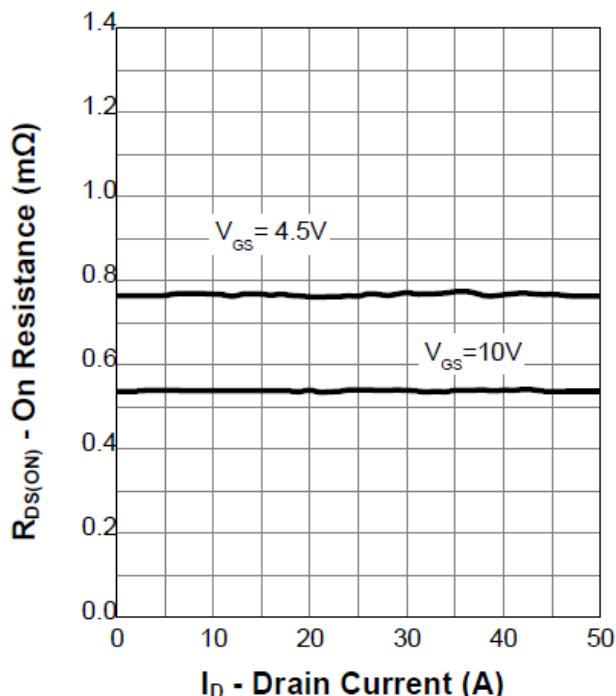




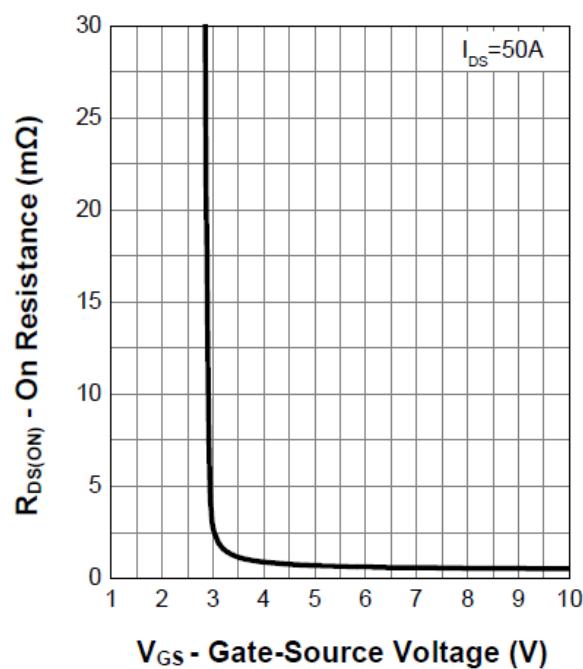
Output Characteristics



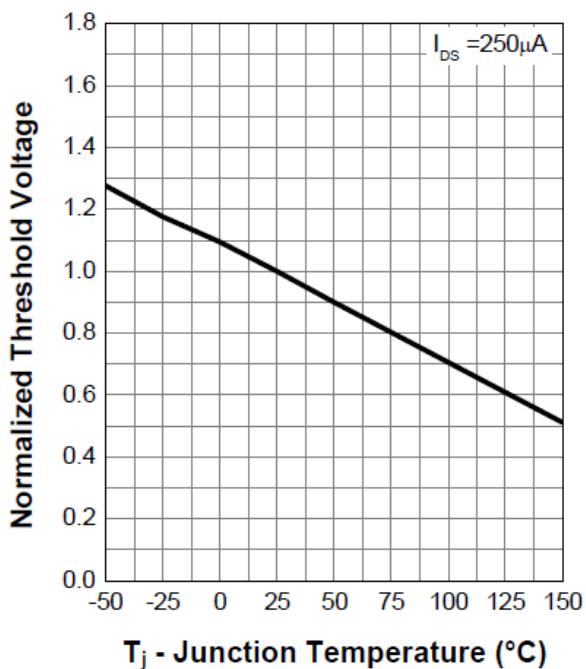
On Resistance

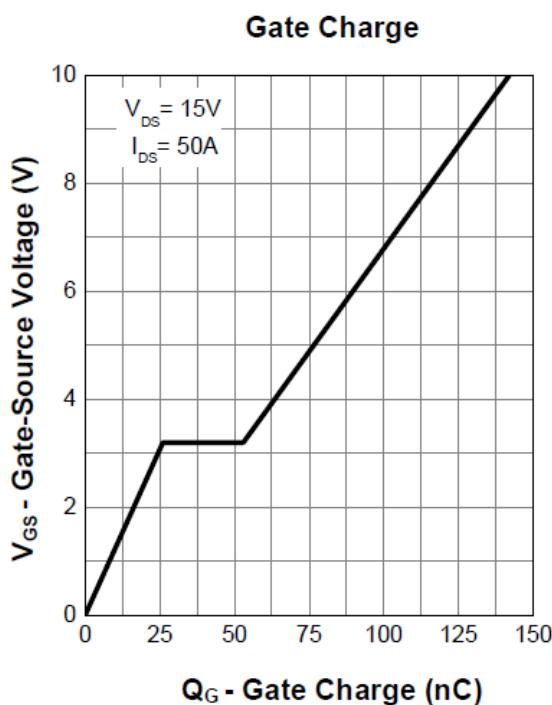
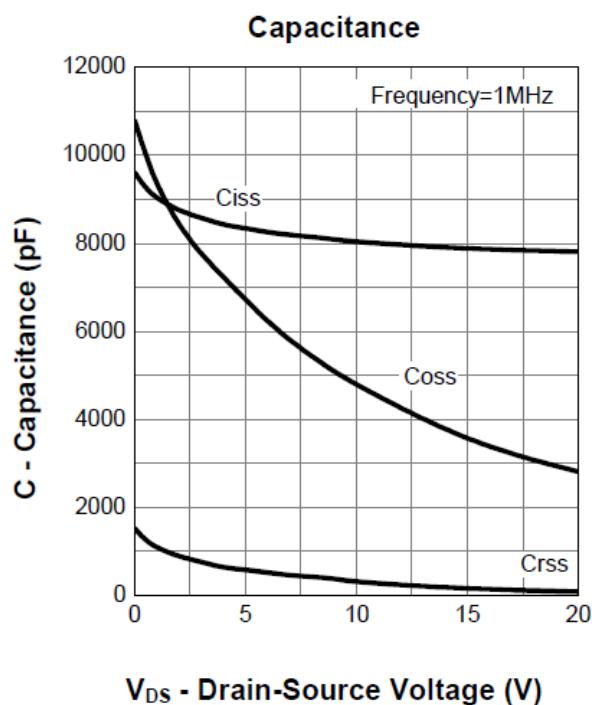
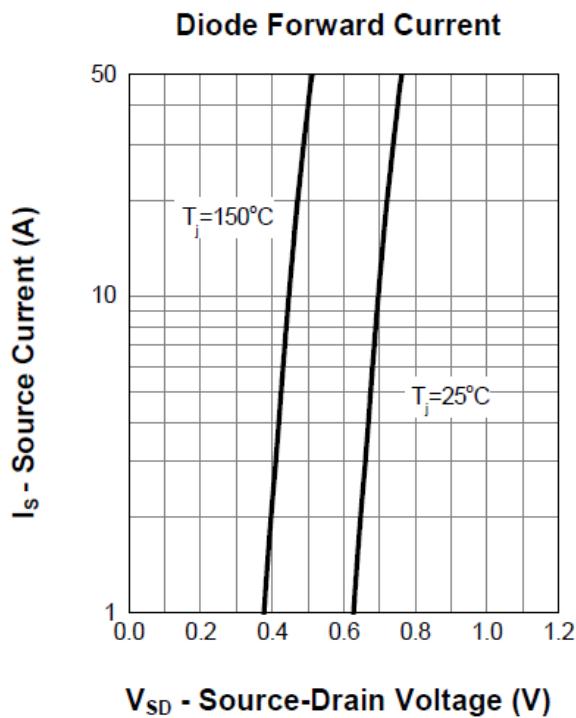
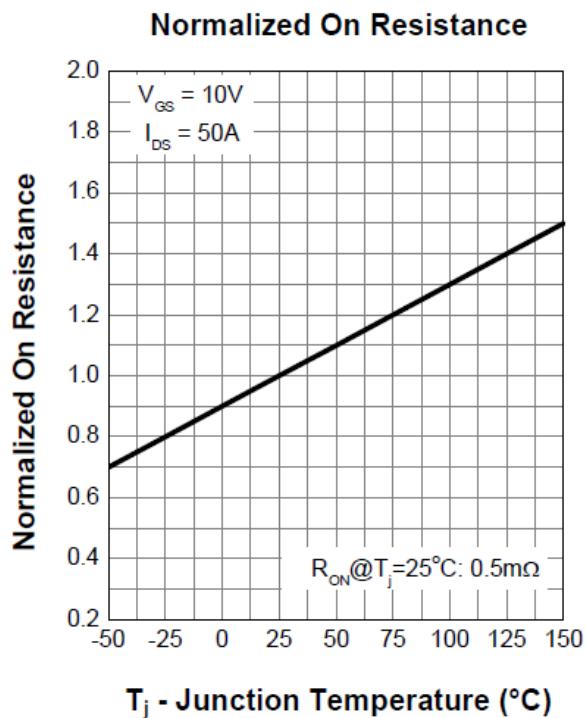


Transfer Characteristics



Normalized Threshold Voltage

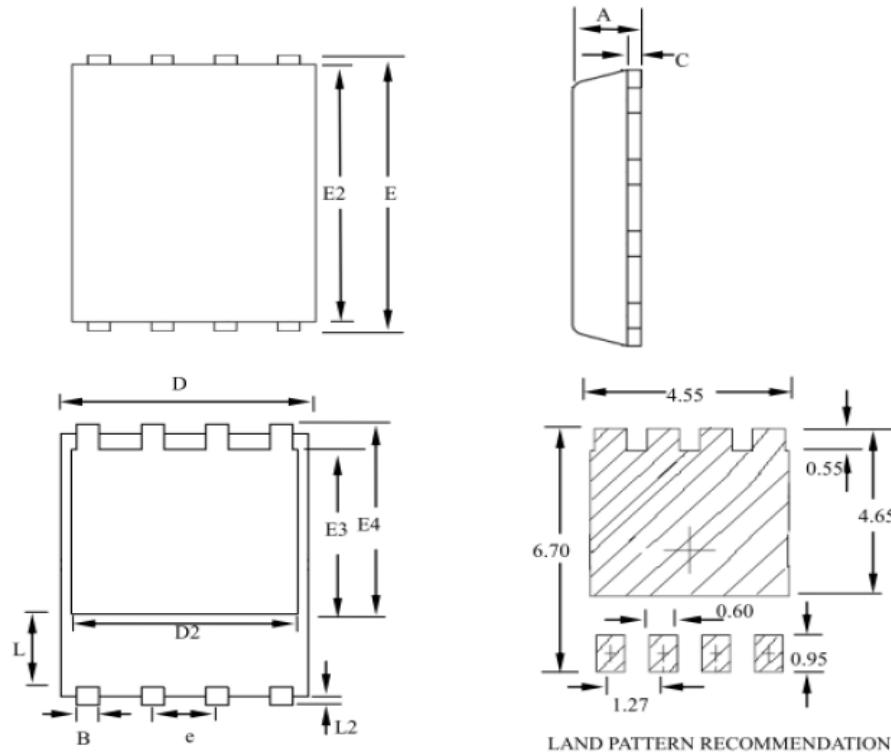






Ordering Information

Part Number	Package code	Packaging
HSBA005N03	PRPAK5*6	5000/Tape&Reel



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	--	1.20	0.031	--	0.047
B	0.30	--	0.51	0.012	--	0.020
C	0.15	--	0.35	0.006	--	0.014
D	4.80	--	5.30	0.189	--	0.209
D2	3.61	--	4.35	0.142	--	0.171
E	5.90	--	6.35	0.232	--	0.250
E2	5.42	--	5.90	0.213	--	0.232
E3	3.23	--	3.90	0.127	--	0.154
E4	3.69	--	4.55	0.145	--	0.179
L	0.61	--	1.80	0.024	--	0.071
L2	0.05	--	0.36	0.002	--	0.014
e	--	1.27	--	--	0.050	--